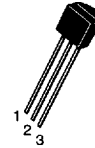
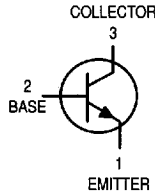


**Amplifier Transistor**  
NPN Silicon

**MPSA20**



CASE 29-04, STYLE 1  
TO-92 (TO-226AA)

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	4.0	Vdc
Collector Current — Continuous	$I_C$	100	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}^{(1)}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage <sup>(2)</sup> ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	40	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 100 \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ Vdc}, I_E = 0$ )	$I_{CBO}$	—	100	nAdc

- $R_{\theta JA}$  is measured with the device soldered into a typical printed circuit board.
- Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain <sup>(2)</sup> (I <sub>C</sub> = 5.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> )	h <sub>FE</sub>	40	400	—
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	—	0.25	V <sub>dc</sub>
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current–Gain — Bandwidth Product <sup>(2)</sup> (I <sub>C</sub> = 5.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	125	—	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	—	4.0	pF

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

EQUIVALENT SWITCHING TIME TEST CIRCUITS

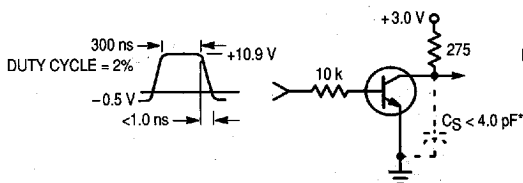


Figure 1. Turn-On Time

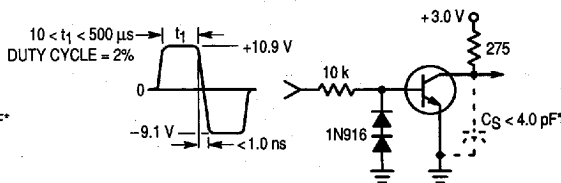


Figure 2. Turn-Off Time

\*Total shunt capacitance of test jig and connectors

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TYPICAL NOISE CHARACTERISTICS

(V<sub>CE</sub> = 5.0 Vdc, T<sub>A</sub> = 25°C)

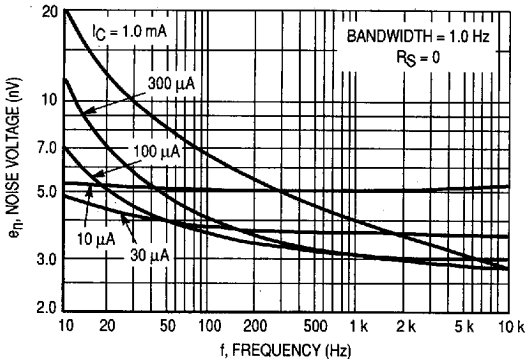


Figure 3. Noise Voltage

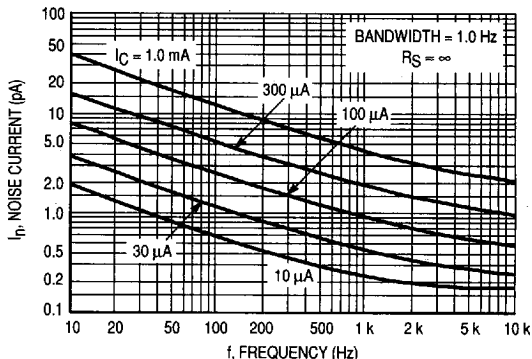


Figure 4. Noise Current

NOISE FIGURE CONTOURS

(V<sub>CE</sub> = 5.0 Vdc, T<sub>A</sub> = 25°C)

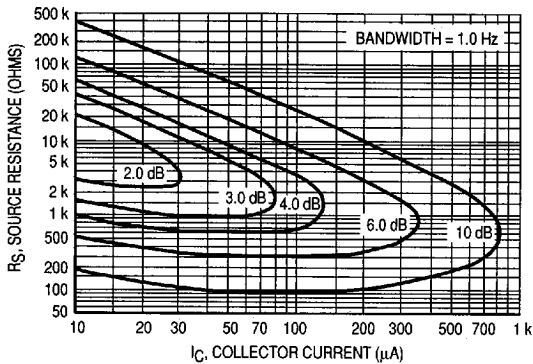


Figure 5. Narrow Band, 100 Hz

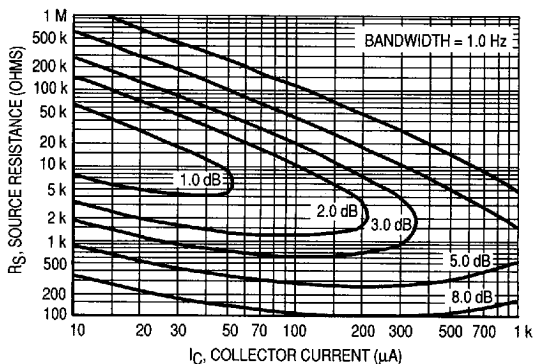


Figure 6. Narrow Band, 1.0 kHz

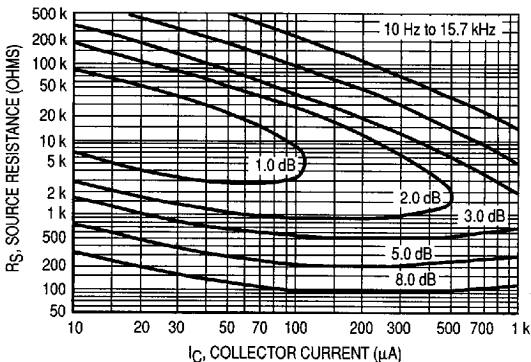


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

e<sub>n</sub> = Noise Voltage of the Transistor referred to the input. (Figure 3)

I<sub>n</sub> = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant (1.38 x 10<sup>-23</sup> j°K)

T = Temperature of the Source Resistance (°K)

R<sub>S</sub> = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

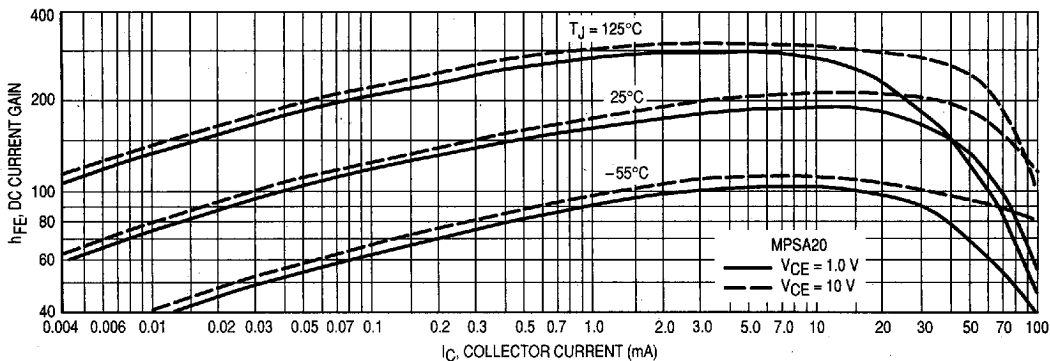


Figure 8. DC Current Gain

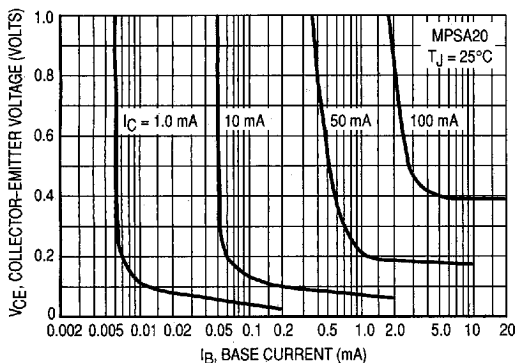


Figure 9. Collector Saturation Region

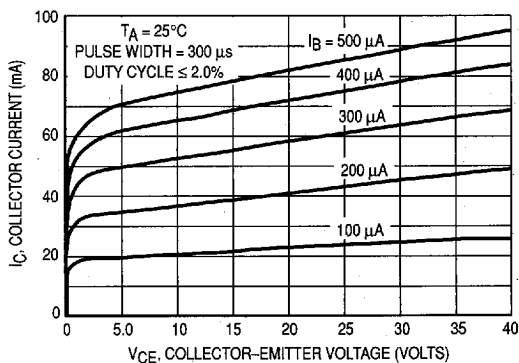


Figure 10. Collector Characteristics

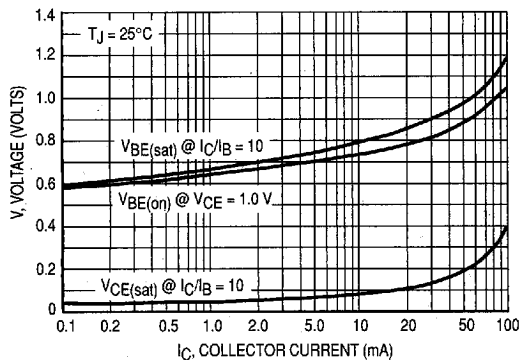


Figure 11. "On" Voltages

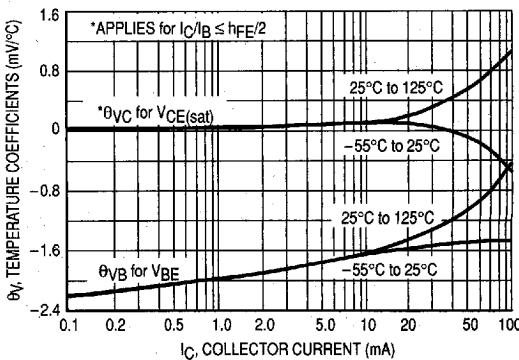


Figure 12. Temperature Coefficients

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TYPICAL DYNAMIC CHARACTERISTICS

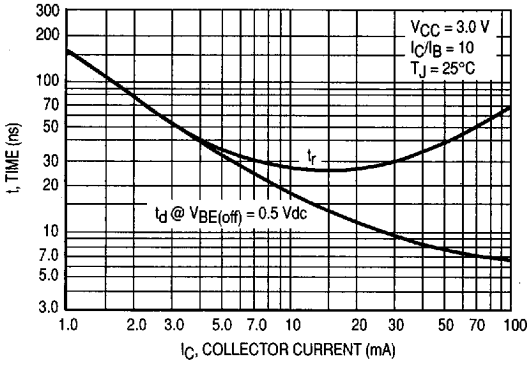


Figure 13. Turn-On Time

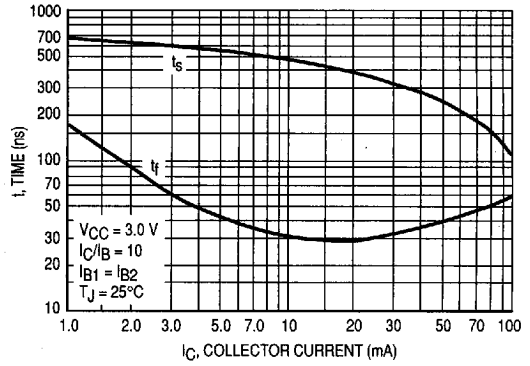


Figure 14. Turn-Off Time

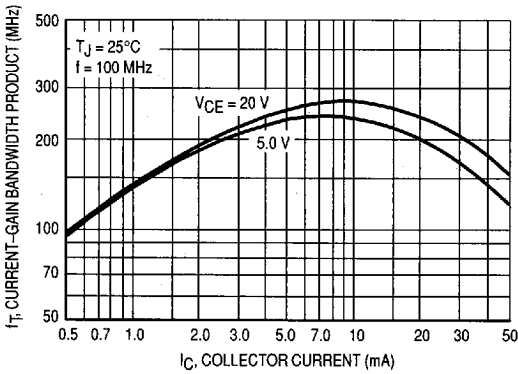


Figure 15. Current-Gain — Bandwidth Product

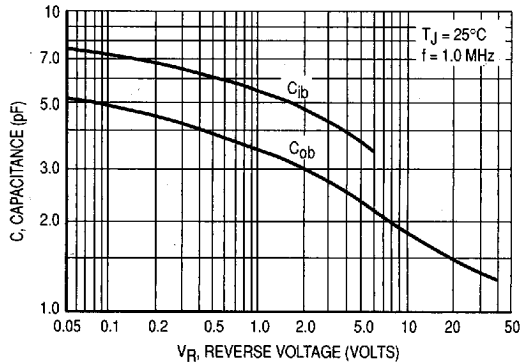


Figure 16. Capacitance

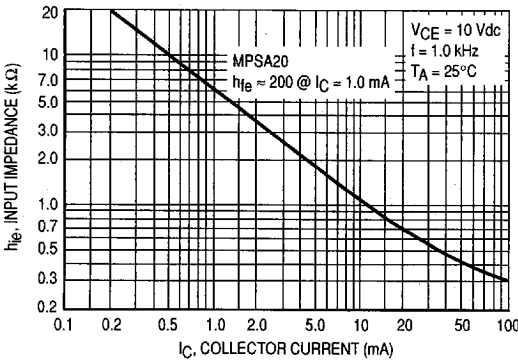


Figure 17. Input Impedance

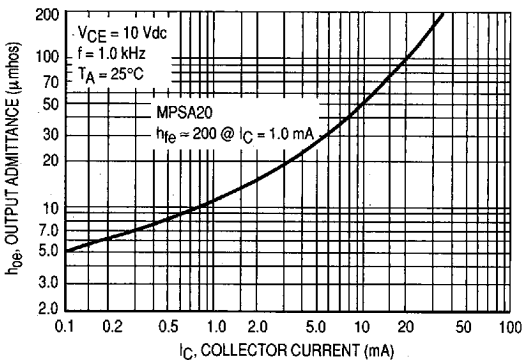


Figure 18. Output Admittance

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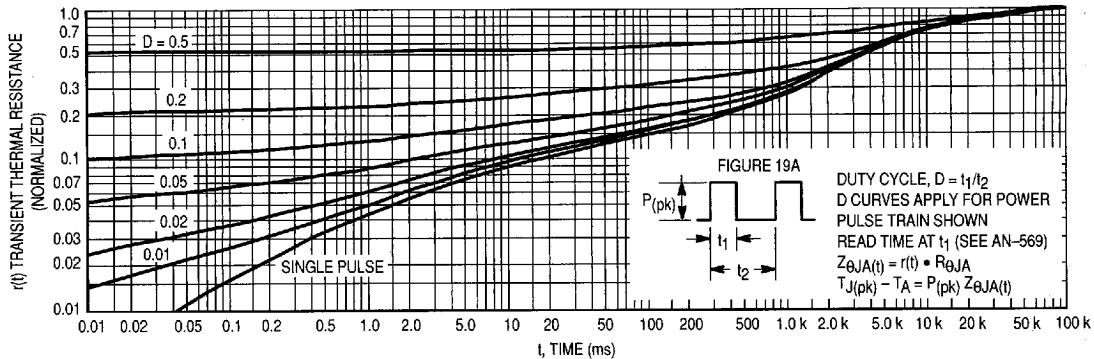


Figure 19. Thermal Response

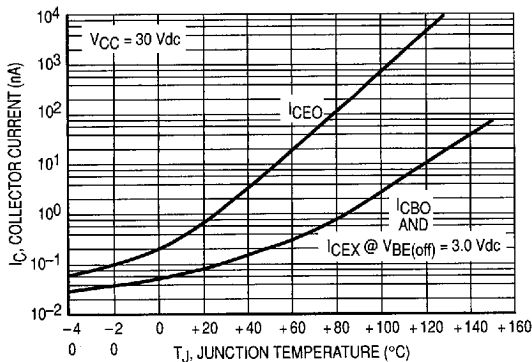


Figure 19A.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find  $Z_{\theta JA}(t)$ , multiply the value obtained from Figure 19 by the steady state value  $R_{\theta JA}$ .

Example:

Dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$  ms,  $t_2 = 5.0$  ms. ( $D = 0.2$ )

Using Figure 19 at a pulse width of 1.0 ms and  $D = 0.2$ , the reading of  $r(t)$  is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P(pk) \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see AN-569.

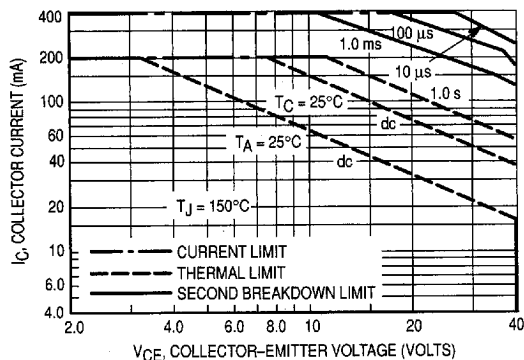


Figure 20.

The safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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